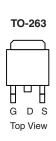


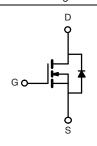
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Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	100	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0105	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0120	
I _D (A)	100	
Configuration	Single	





N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM100N10-10-GE3

ABSOLUTE MAXIMUM RATING	GS (T _C = 25 °C, unles	s otherwise noted	<u>(h</u>	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C ^a	1	100	
Continuous Drain Current	T _C = 125 °C	l _D	70	
Continuous Source Current (Diode Conduction) ^a		I _S	100	Α
Pulsed Drain Current ^b		I _{DM}	400	
Single Pulse Avalanche Current		I _{AS}	75	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	280	mJ
Maximum Dawar Dissipationh	T _C = 25 °C	D.	375	14/
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125	W
Operating Junction and Storage Temperation	ure Range	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						L	l
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α
		V _{GS} = 10 V	I _D = 30 A	-	0.0070	0.0105	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0200	Ω
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0260	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0080	0.0120	
Forward Transconductance ^b	9 _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	115	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	6440	8050	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	655	820	pF
Reverse Transfer Capacitance	C _{rss}	1		-	315	395	
Total Gate Charge ^c	Qg			-	122	185	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 85 \text{ A}$	-	23	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	28	-	
Gate Resistance	R _g		f = 1 MHz	0.70	1.41	2.30	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	13	20	
Rise Time ^c	t _r	V _{DD} :	= 50 V, $R_L = 0.6 \Omega$	-	14	21	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 85 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ - 44		66	ns		
Fall Time ^c	t _f				10	15	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	400	Α
Forward Voltage	V _{SD}	I _F =	85 A, V _{GS} = 0 V	-	0.9	1.5	V

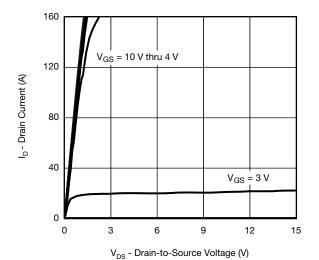
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

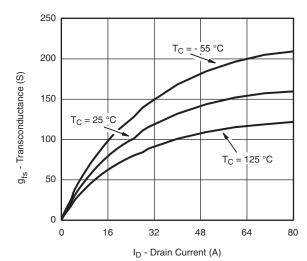
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



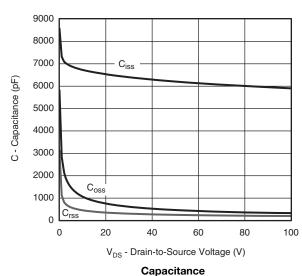
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

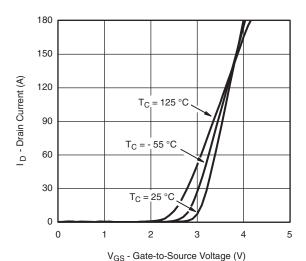


Output Characteristics

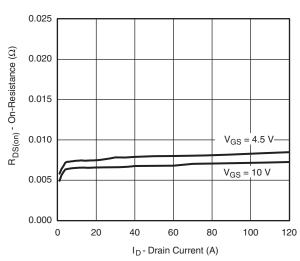


Transconductance

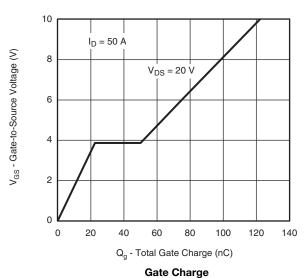




Transfer Characteristics



On-Resistance vs. Drain Current

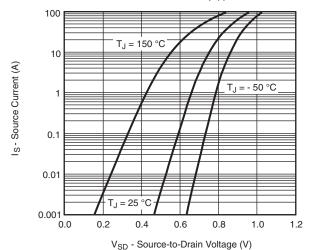


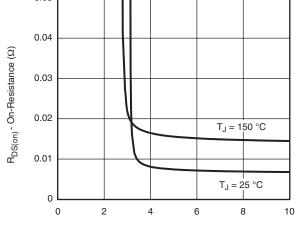
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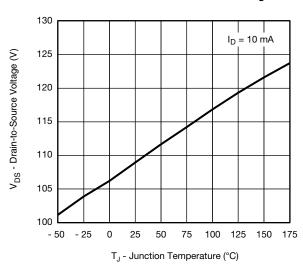
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



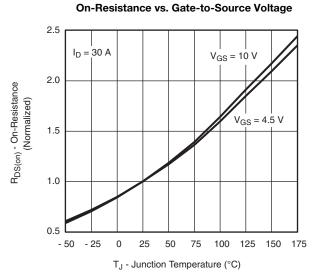


 V_{GS} - Gate-to-Source Voltage (V)

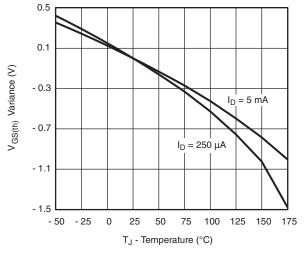
Source Drain Diode Forward Voltage



Breakdown Voltage vs. Junction Temperature

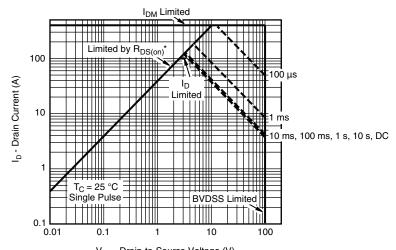


Normalized On-Resistance vs. Junction Temperature



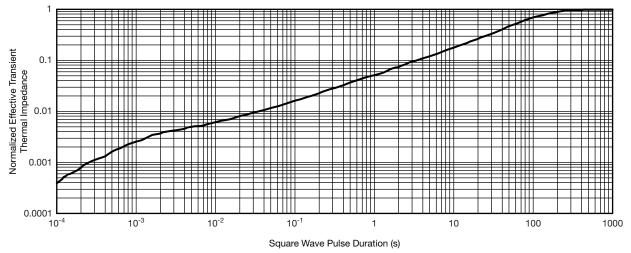
Threshold Voltage Variance vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



 $$V_{DS}$$ - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

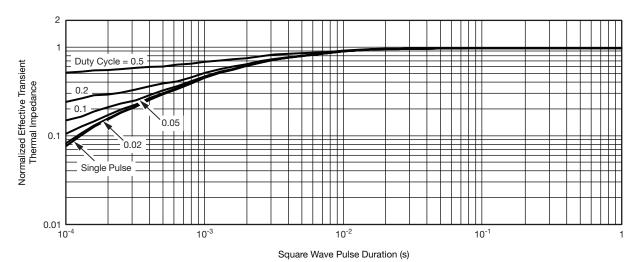
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

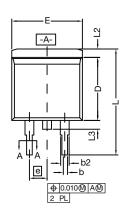
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

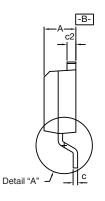
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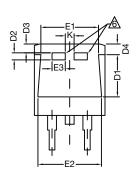
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TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T









DETAIL A (ROTATED 90°)



≥ <u>↓</u>			ţ
< T		10	ပ
SF	CTION	1	1

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

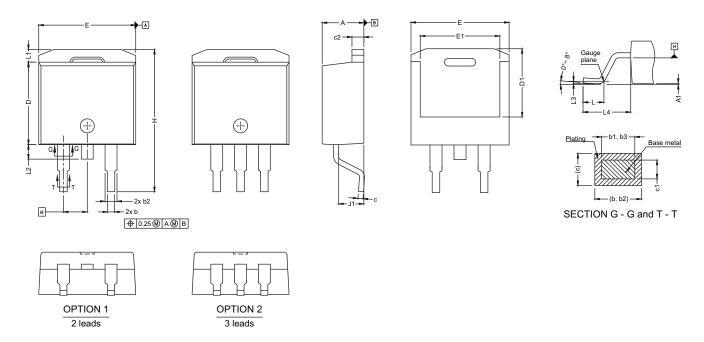
		INCHES		MILLIN	METERS	
	DIM.	MIN.	MAX.	MIN.	MAX.	
A		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
b1		0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
C*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	<u>E1</u>	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54	BSC	
K 0.045 0.055		0.055	1.143	1.397		
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010	BSC	0.254	BSC	
	М	-	0.002	-	0.050	



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VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25	5 typ.
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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